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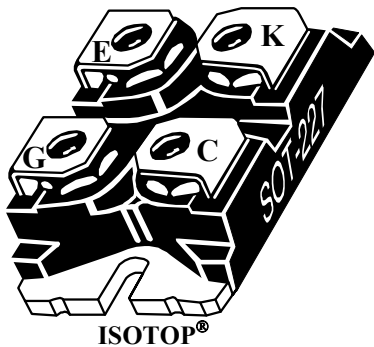
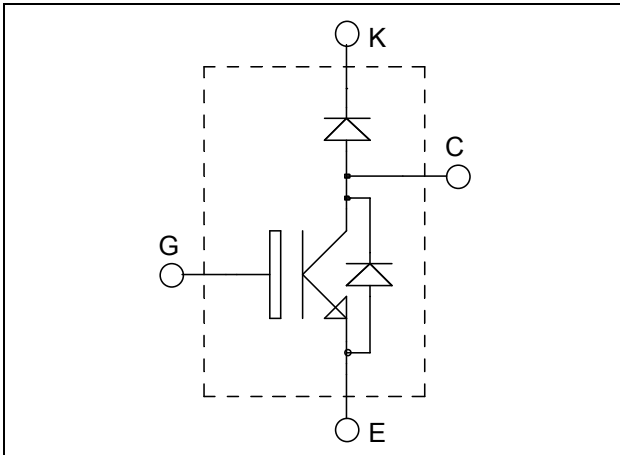
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



**ISOTOP<sup>®</sup> Boost chopper  
Trench + Field Stop IGBT4  
Power module**

**$V_{CES} = 1200V$   
 $I_C = 40A @ T_c = 80^{\circ}C$**



### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

### Features

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

### Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_c$  of  $V_{CEsat}$
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_C$	Continuous Collector Current	$T_c = 25^{\circ}C$	65
		$T_c = 80^{\circ}C$	40
$I_{CM}$	Pulsed Collector Current	$T_c = 25^{\circ}C$	70
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	220
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	70A @ 1100V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			250	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 35A$		1.85 2.25	2.25	V
		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$				
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.2mA$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		1950		pF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		155		
$C_{res}$	Reverse Transfer Capacitance	$f = 1MHz$		115		
$Q_G$	Gate charge	$V_{GE} = \pm 15V; V_{CE} = 600V$ $I_C = 35A$		0.27		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 35A$ $R_G = 12\Omega$		130		ns
$T_r$	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			300		
$T_f$	Fall Time			45		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 35A$ $R_G = 12\Omega$		150		ns
$T_r$	Rise Time			35		
$T_{d(off)}$	Turn-off Delay Time			350		
$T_f$	Fall Time			80		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 35A$ $R_G = 12\Omega$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	2.6 4		mJ
$E_{off}$	Turn-off Switching Energy		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	2 3		mJ
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 900V$ $t_p \leq 10\mu\text{s}; T_j = 150^\circ\text{C}$		140		A

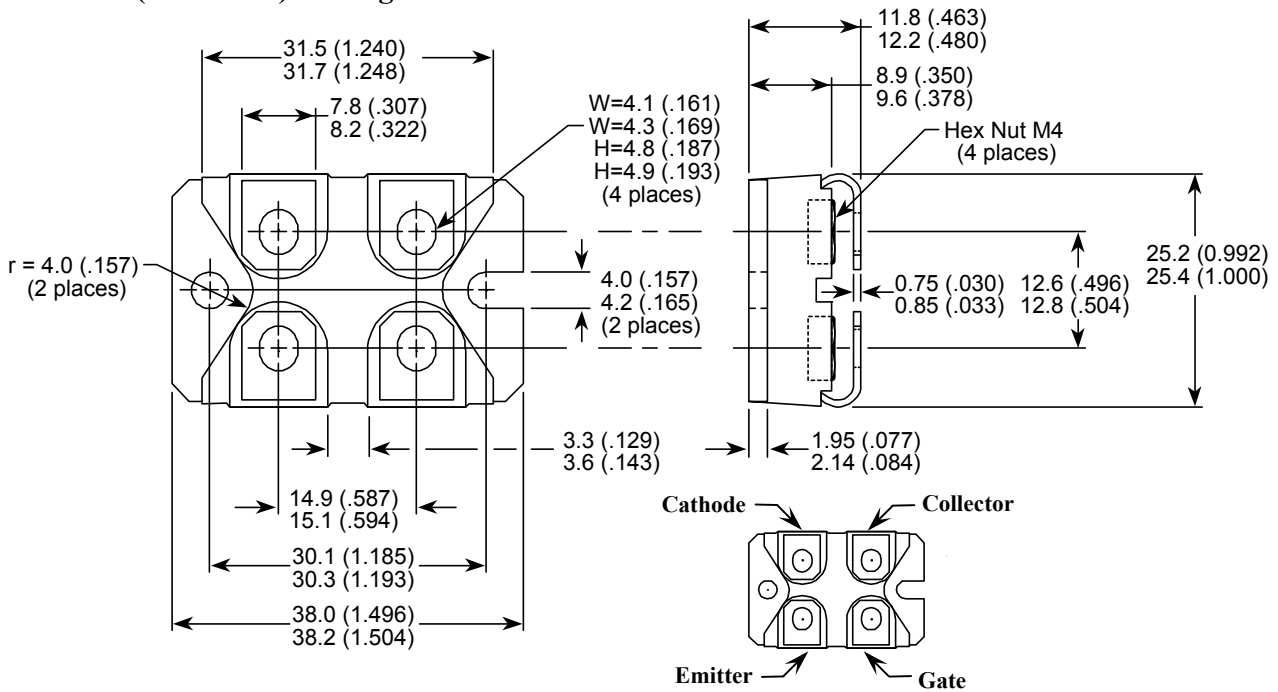
**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$			100 500	$\mu\text{A}$
		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$				
$I_F$	DC Forward Current	$T_c = 80^\circ\text{C}$		30		A
$V_F$	Diode Forward Voltage	$I_F = 30A$		2.6	3.1	V
		$I_F = 60A$		3.2		
		$I_F = 30A$	$T_j = 125^\circ\text{C}$		1.8	
$t_{rr}$	Reverse Recovery Time	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	300 380		ns
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	360 1700		nC

## Thermal and package characteristics

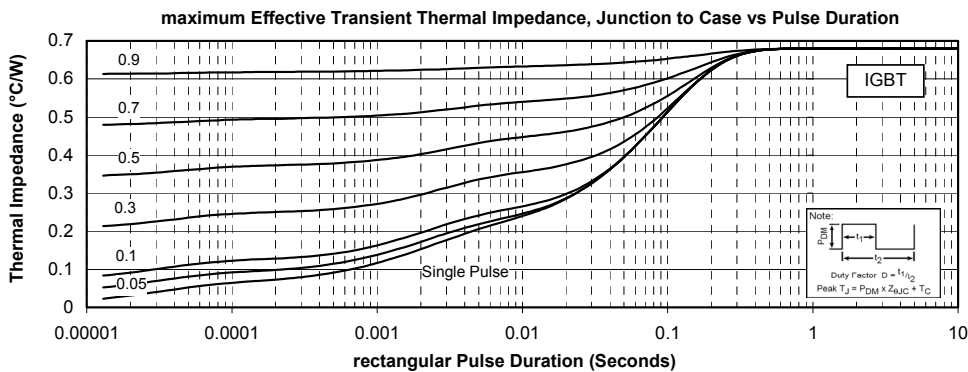
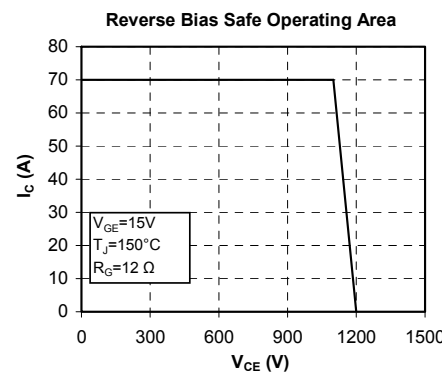
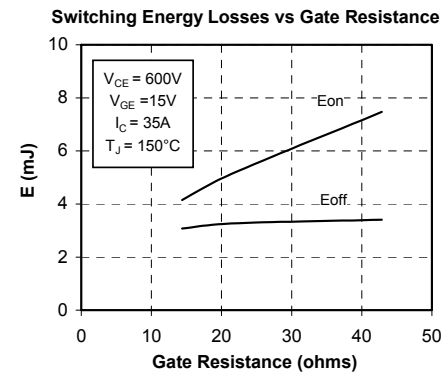
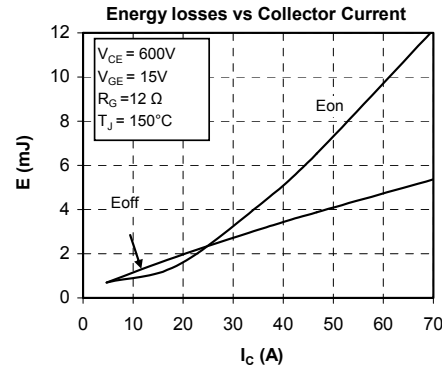
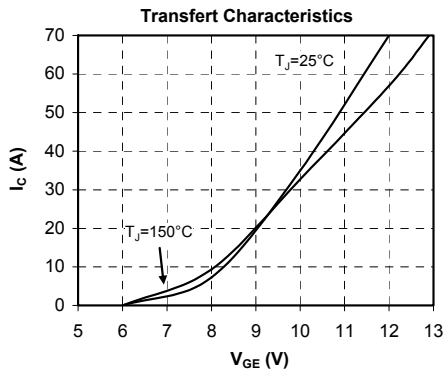
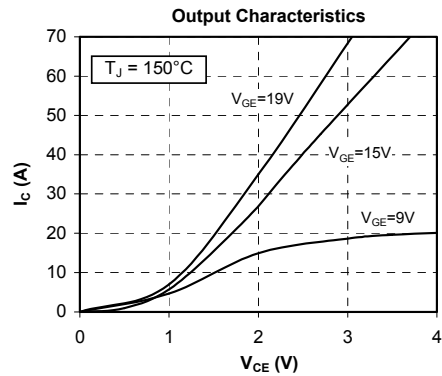
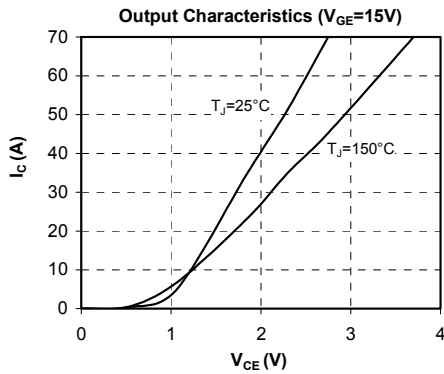
Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.68	°C/W
		Diode		1.2	
R <sub>thJA</sub>	Junction to Ambient (IGBT & Diode)			20	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	2500			V
T <sub>J</sub> , T <sub>STG</sub>	Storage Temperature Range	-55		175	°C
T <sub>L</sub>	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

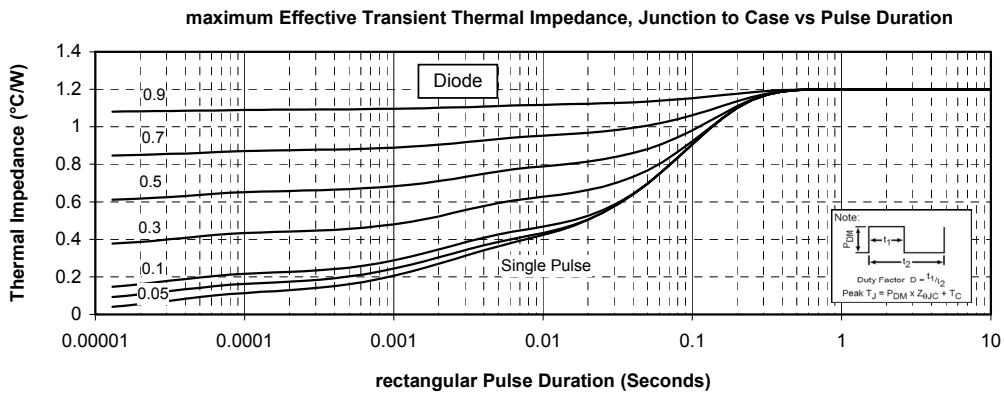
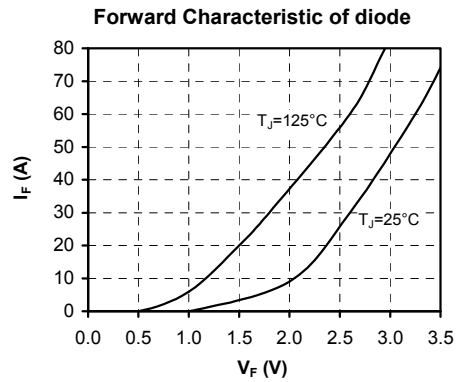
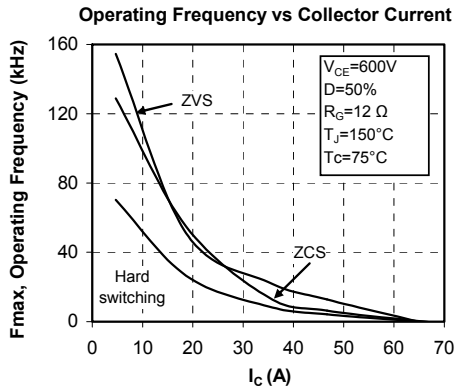
## SOT-227 (ISOTOP®) Package Outline



ISOTOP® is a registered trademark of ST Microelectronics NV

## Typical Performance Curve





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